



SANYO Semiconductors

DATA SHEET

MCH6649 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- 1.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-200	mA
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-800	mA
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	0.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-100mA	190	320		mS
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-100mA, V _{GS} =-4V		1.8	2.4	Ω
	R _{DS(on)2}	I _D =-50mA, V _{GS} =-2.5V		2.4	3.4	Ω
	R _{DS(on)3}	I _D =-10mA, V _{GS} =-1.5V		4.5	9.0	Ω

Marking : XA

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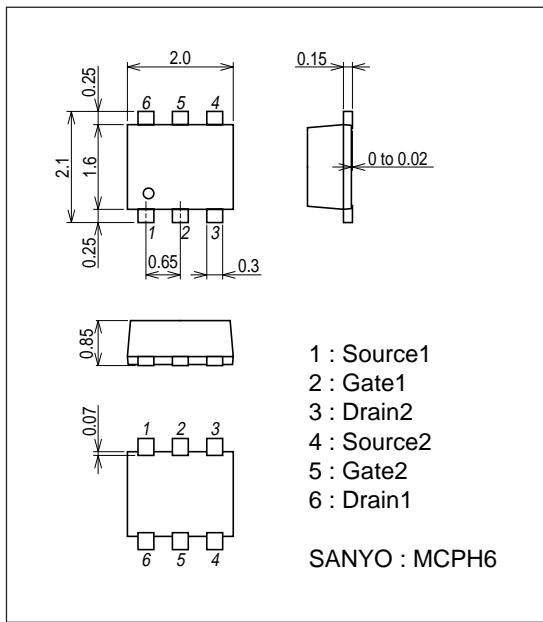
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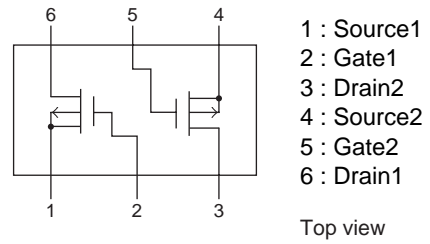
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		35		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		7.2		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		2.1		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		75		ns
Rise Time	t _r	See specified Test Circuit.		170		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		550		ns
Fall Time	t _f	See specified Test Circuit.		350		ns
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.58		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.17		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-4V, I _D =-200mA		0.12		nC
Diode Forward Voltage	V _{SD}	I _S =-200mA, V _{GS} =0V	-0.89		-1.2	V

Package Dimensions

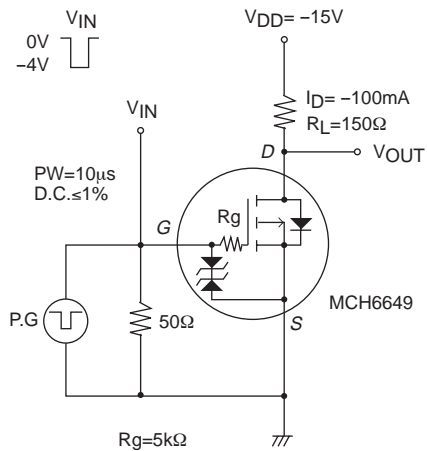
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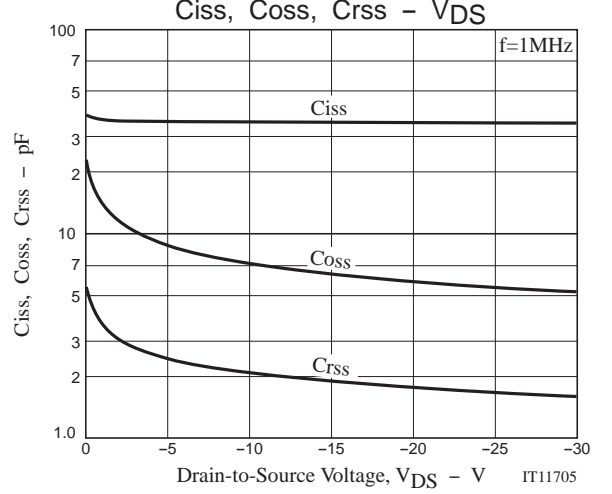
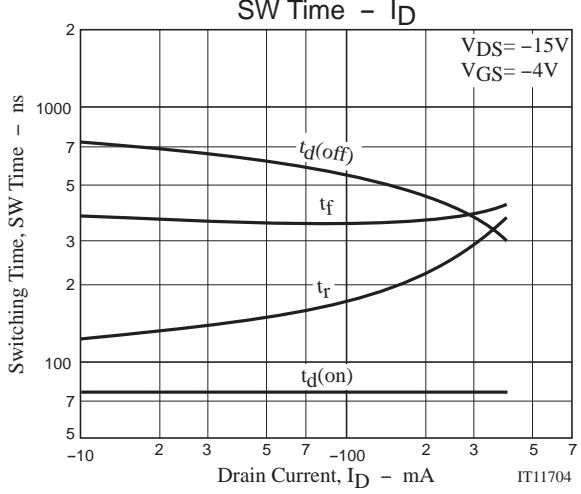
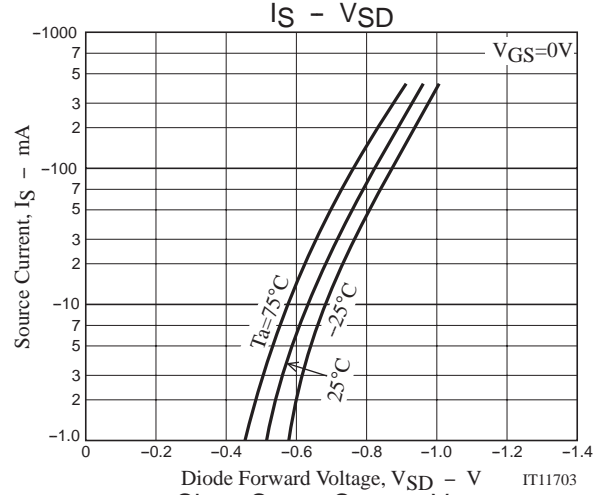
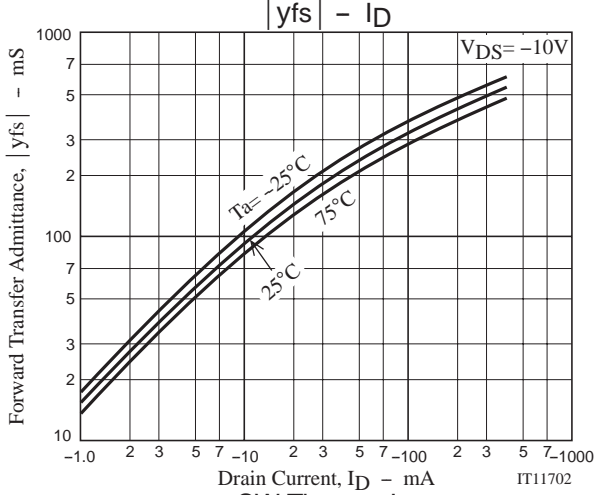
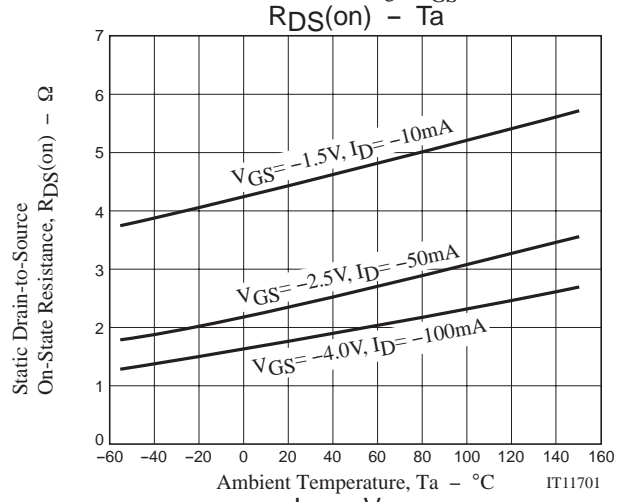
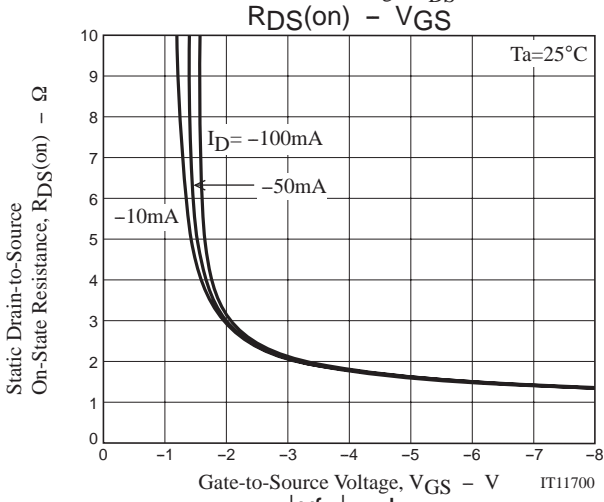
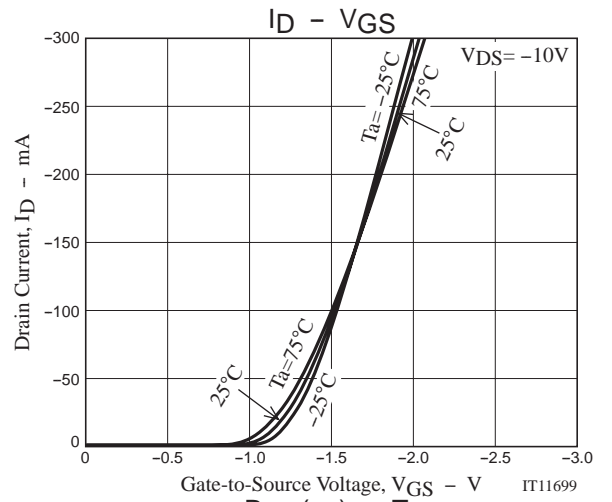
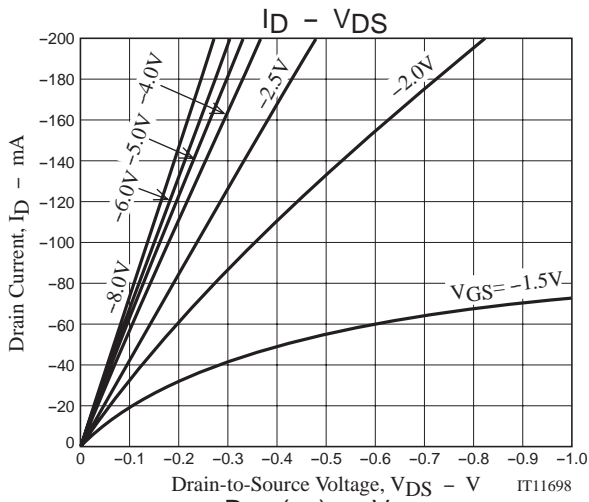
Electrical Connection

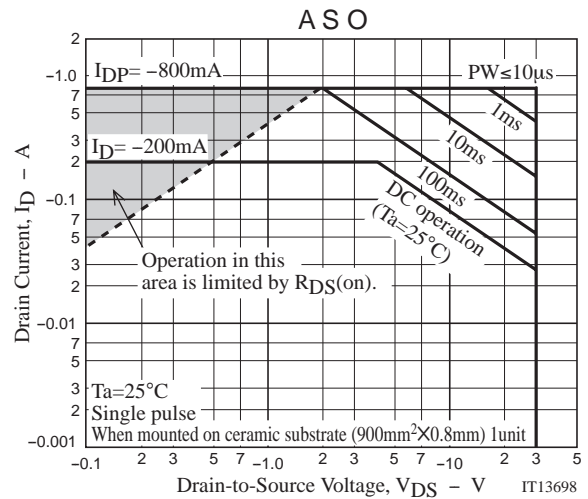
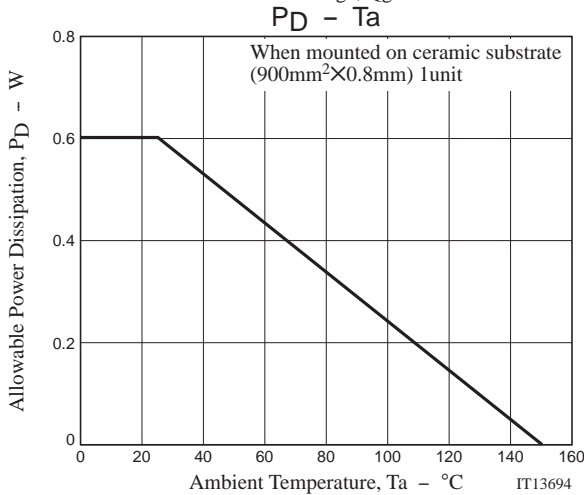
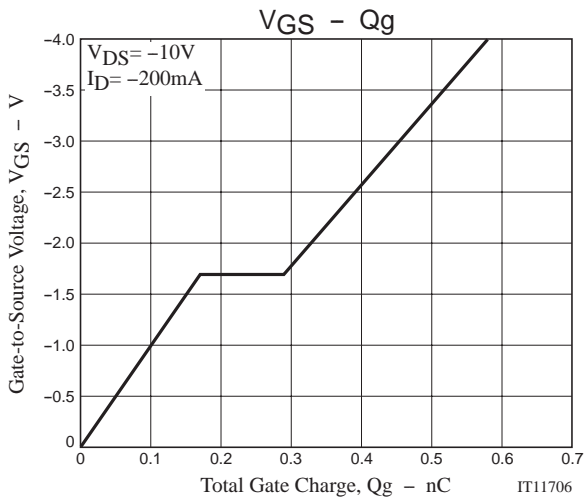


Switching Time Test Circuit



MCH6649





Note on usage : Since the MCH6649 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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